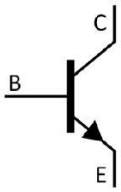
VRW0;< ṂṂ Ḅ QSQ ÆṀ ч s Ⅱ ㄱ Silicon NPN transistor in a SOT-89 Plastic Package.

ت ⊐ я ∪ Ӈ ı Ɔ Ⅼ ⅇ ı ṇ ғ β

Low $V_{CE(sat)}$, high current, HF Product.

₹ ˇ ˉ ˍ Ầ ԋ ı ὺ Ǐ ~ ʜ [OBJ] ὖ ˇ Ł ˝ ı ㅓ ớ Ầ ԋ Ɔ ◊

General purpose switching and muting, LCD back-lighting, supply line switching circuits.



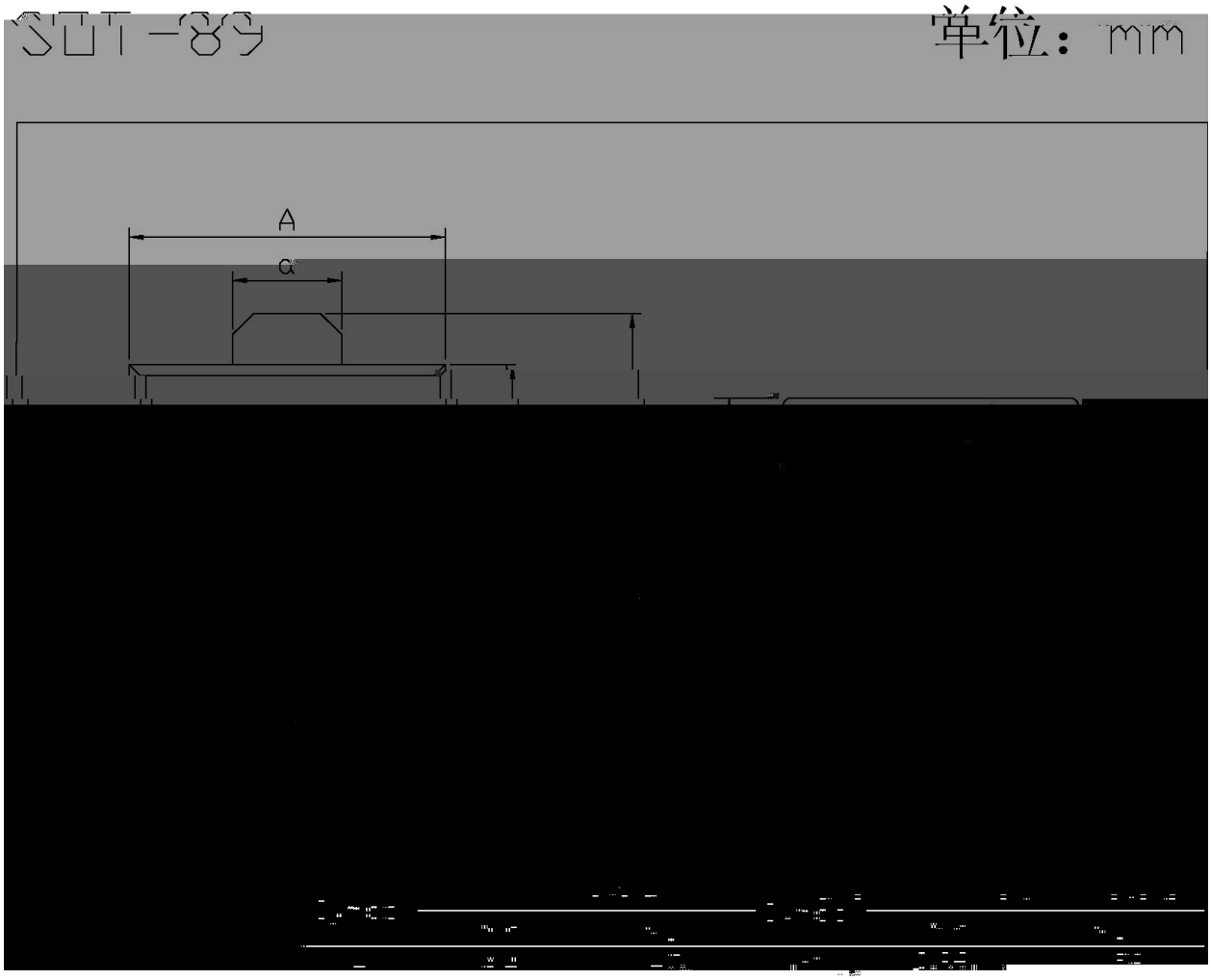
v ‴Ω Parameter	ϒ ᴺ Symbol	‴Ω Ö Rating	ᴅ Ꮋ Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	3	A
Collector Base - Continuous	I_B	0.5	A
Peak Collector Current	I_{CM}	5	A
Total Power Dissipation	P_{tot} ⊦⁴	550	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-65 150	

4 λ ᴴ ϯ Ḡ Ł ϱ м ↄ ت — ⅈ

v ‴Ω Parameter	ϒ ᴺ Symbol	V ⅄ ⁝ᵀ ϯ Test Conditions	ω ṇ Ö Min	Ɛ ʒ Ö Typ	ω ᶻ Ö Max	ᴅ Ꮋ Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=50V I_E=0			100	nA
Collector Cut-Off Current	I_{CBO}	V_{CB}=50V I_E=0 T_j=150			50	A
Collector Cut-Off Current	I_{CES}	V_{CE}=50V V_{BE}=0			100	nA
Emitter Base Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			100	nA
F5(3)*	$h_{FE(1)}$	V_{CE}^{CE}=2.0V I_C=0.1A	300			
	$h_{FE(2)}$	V_{CE}=2.0V I_C=0.5A	300			
DC Current Gain	$h_{FE(3)*}$	V_{CE}=2.0V I_CŦ1.0A	300		700	

/ Electrical Characteristic Curve

/ Package Dimensions



PBSS4350X

Rev.G Jul.-2025

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)

ب ˝ χ

1 Ĺ ♬ □ ỷ 150 Ḱ 180 ɬ ı `H ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 245 ° 5 ɬ ı `H ڑ `Y ʌ ʁ 5 ° 0.5sec;

3 ì ˙ ٢ ˛ ɔ ﻩ ỷ ʁ 2 Ḱ 10 ɬ /sec.

Note:

1.Preheating:150~180 ɬ , Time:60~90sec.

2.Peak Temp.:245 ° 5 ɬ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɬ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 260 ° 5 ɬ	`H ڑ χ 10 ° 1 sec.	Temp.:260±5	Time:10±1 sec

/ Packaging SPEC.

ი ` ɣ Ь / REEL

Package Type	Units	Dimension	(unit mm³)